

# MSKSEMI

SEMICONDUCTOR



ESD



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PLED

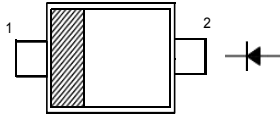
Product data sheet

[www.msksemi.com](http://www.msksemi.com)

## Surface Mount Schottky Barrier Diodes

### Features

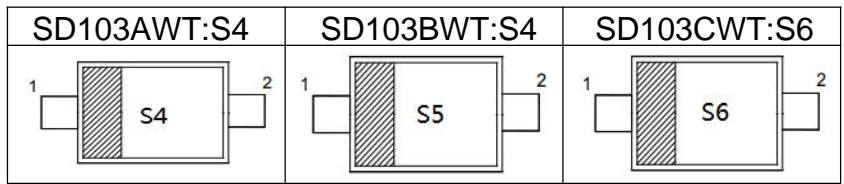
- Low Forward Voltage



### MARK:

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



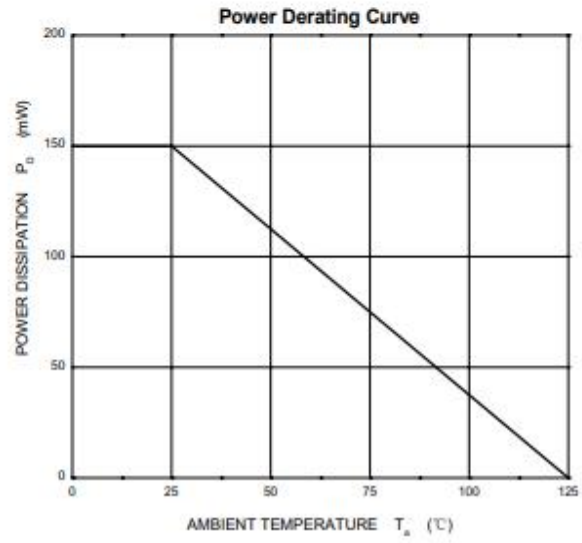
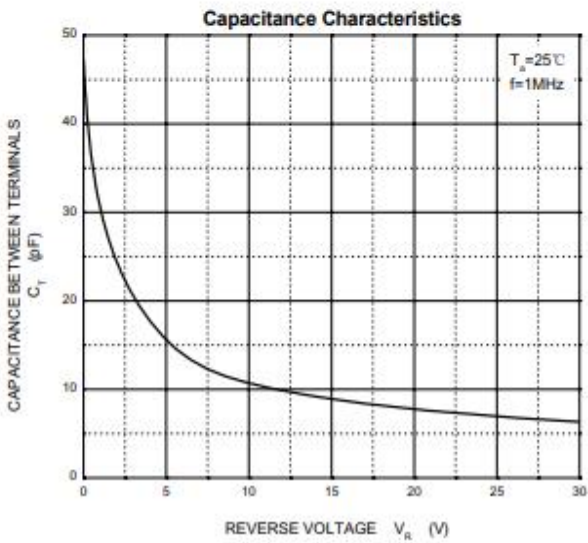
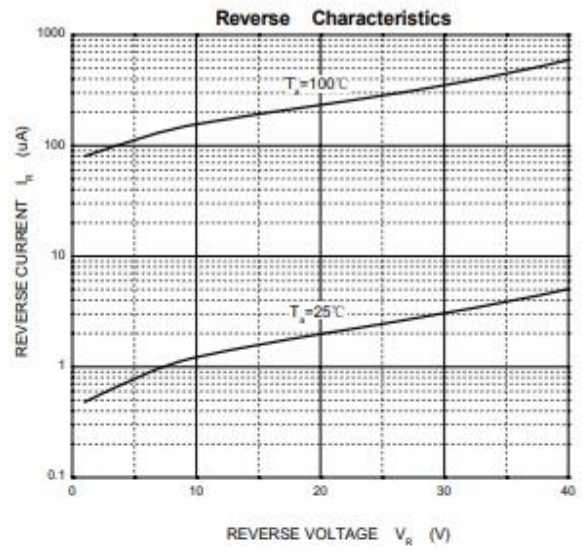
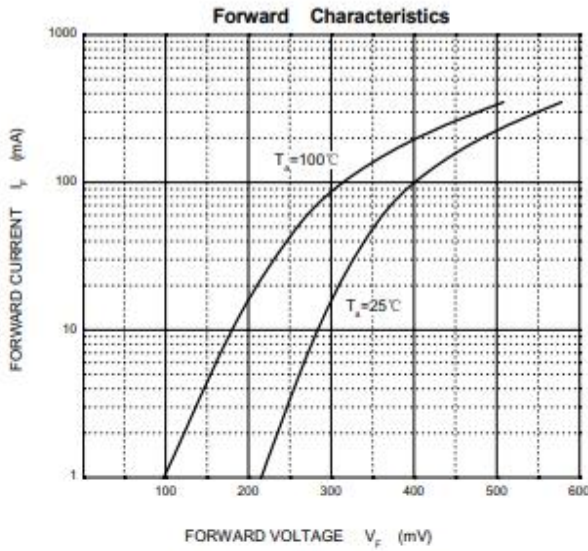
### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	SD103AWT SD103BWT SD103CWT	40 30 20	V	
Reverse Voltage		V <sub>R</sub>	SD103AWT SD103BWT SD103CWT	40 30 20	V
Average Forward Rectified Current		I <sub>F(AV)</sub>		350	mA
Non-Repetitive Peak Forward Surge Current at t = 1 s	I <sub>FSM</sub>		2	A	
Power Dissipation	P <sub>tot</sub>		200	mW	
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>		- 65 to + 125	°C	

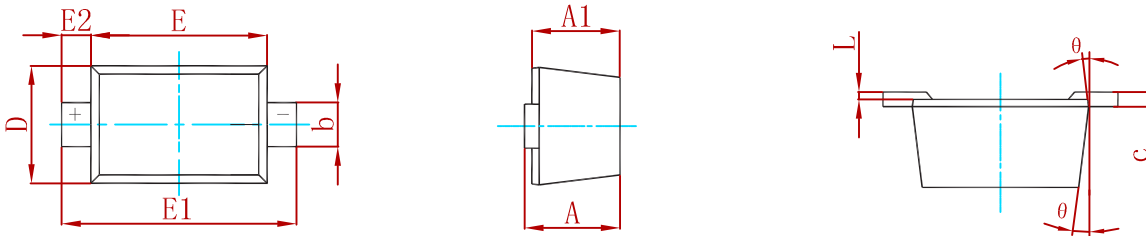
### Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Reverse Breakdown Voltage at I <sub>R</sub> = 10 μA	V <sub>(BR)R</sub>	SD103AWT SD103BWT SD103CWT	40 30 20	- - -	V	
Reverse Leakage Current at V <sub>R</sub> = 30V at V <sub>R</sub> = 20 V at V <sub>R</sub> = 10 V		I <sub>R</sub>	- - -	- - -	5 5 5	μA
Forward Voltage at I <sub>F</sub> = 20 mA at I <sub>F</sub> = 200 mA		V <sub>F</sub>	- -	- -	0.37 0.6	V
Total Capacitance at V <sub>R</sub> = 0 V, f = 1 MHz	C <sub>T</sub>	-	50	-	pF	
Reverse Recovery Time at I <sub>F</sub> = I <sub>R</sub> = 200 mA, I <sub>rr</sub> = 0.1 I <sub>R</sub> , R <sub>L</sub> = 100 Ω	t <sub>rr</sub>	-	10	-	ns	

Typical Characteristics

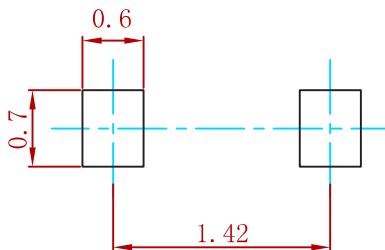


**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.510	0.770	0.020	0.031
A1	0.500	0.700	0.020	0.028
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	0.750	0.850	0.030	0.033
E	1.100	1.300	0.043	0.051
E1	1.500	1.700	0.059	0.067
E2	0.200 REF		0.008 REF	
L	0.010	0.070	0.001	0.003
θ	7° REF		7° REF	

**Suggested Pad Layout**



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05mm.
3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
SD103AWT/SD103BWT/SD103CWT	SOD-523	3000

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